L15   ANSWER 5 OF 12 HCAPLUS   COPYRIGHT 2003 ACS on STN
AN   2001:592177 HCAPLUS
DN   135:173867
TI   Remote plasma cleaning method for semiconductor processing chambers
IN   Rajagopalan, Ravi; Liu, Patricia M.; Narwankar, Pravin K.; Tran, Huyen;
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PA   Applied Materials, Inc., USA
SO   U.S., 26 pp., Cont.-in-part of U.S. 6,125,859.
      CODEN: USXXAM
DT   Patent
LA   English
IC   ICM H05H001-00
NCL   216067000
CC   76-11 (Electric Phenomena)
      Section cross-reference(s): 47, 75
FAN.CNT 4

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 6274058	B1	20010814	US 1999-347236	19990702
	US 6125859	A	20001003	US 1997-893922	19970711
	TW 385494	B	20000321	TW 1998-87111364	19980713
	EP 1065295	A1	20010103	EP 2000-113942	20000630
	R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO				
	JP 2001085418	A2	20010330	JP 2000-201117	20000703
PRAI	US 1997-893922	A2	19970711		
	US 1997-811627	A1	19970305		
	US 1999-347236	A	19990702		

AB   A processing chamber cleaning method is described which uses microwave
      energy to remotely generate a reactive species to be used alone or in
      combination with an inert gas to remove deposits from a processing
      chamber. The reactive species can remove deposits from a 1st processing
      region at a 1st pressure and then remove deposits from a 2nd processing
      region at a 2nd pressure. Also described is a cleaning process using
      remotely generated reactive species in a single processing region at 2
      different pressures. Addnl., different ratios of reactive gas and inert
      gas may be used to improve the uniformity of the cleaning process,
      increase the cleaning rate, reduce recombination of reactive species and
      increase the residence time of reactive species provided to the processing
      chamber.
      RL: PEP (Physical, engineering or chemical process); PROC (Process)
         (remote plasma cleaning method for semiconductor processing chambers)

RN   172901-22-3 HCAPLUS
CN   Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-,
      (OC-6-23)- (9CI) (CA INDEX NAME)